

Is Now Part of



# **ON Semiconductor**®

To learn more about ON Semiconductor, please visit our website at <u>www.onsemi.com</u>

ON Semiconductor and the ON Semiconductor logo are trademarks of Semiconductor Components Industries, LLC dba ON Semiconductor or its subsidiaries in the United States and/or other countries. ON Semiconductor owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of ON Semiconductor's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. ON Semiconductor reserves the right to make changes without further notice to any products herein. ON Semiconductor makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does ON Semiconductor assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using ON Semiconductor dates sheds, regardless of any support or applications information provided by ON Semiconductor. "Typical" parameters which may be provided in ON Semiconductor dates sheds and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. ON Semiconductor does not convey any license under its patent rights of others. ON Semiconductor products are not designed, intended, or authorized for use on similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use ON Semiconductor and its officers, employees, subsidiaries, affliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out or i, directly or indirectly, any lange of the applicatio customer's to unauthorized use, even if such claim alleges that ON Semiconductor was negligent regarding the



January 2008

# 74LVTH125 Low Voltage Quad Buffer with 3-STATE Outputs

## Features

- Input and output interface capability to systems at 5V V<sub>CC</sub>
- Bushold data inputs eliminate the need for external pull-up resistors to hold unused inputs
- Live insertion/extraction permitted
- Power Up/Down high impedance provides glitch-free bus loading
- Outputs source/sink –32mA/+64mA
- Functionally compatible with the 74 series 125
- Latch-up performance exceeds 500mA
- ESD performance:
  - Human-body model > 2000V
  - Machine model > 200V

Ordering Information

- Charged-device model > 1000V

## **General Description**

The LVTH125 contains four independent non-inverting buffers with 3-STATE outputs.

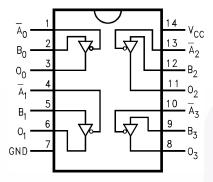
These buffers are designed for low-voltage (3.3V)  $V_{CC}$  applications, but with the capability to provide a TTL interface to a 5V environment. The LVTH125 is fabricated with an advanced BiCMOS technology to achieve high speed operation similar to 5V ABT while maintaining a low power dissipation.

	mation	
Order Number	Package Number	Package Description
74LVTH125M	M14A	14-Lead Small Outline Integrated Circuit (SOIC), JEDEC MS-012, 0.150" Narrow
74LVTH125SJ	M14D	14-Lead Small Outline Package (SOP), EIAJ TYPE II, 5.3mm Wide
74LVTH125MTC	MTC14	14-Lead Thin Shrink Small Outline Package (TSSOP), JEDEC MO-153, 4.4mm Wide

Device also available in Tape and Reel. Specify by appending suffix letter "X" to the ordering number.

All packages are lead free per JEDEC: J-STD-020B standard.

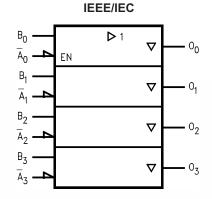
# **Connection Diagram**



# **Pin Description**

Pin Names	Description
Ā <sub>n</sub> , B <sub>n</sub>	Inputs
O <sub>n</sub>	3-STATE Outputs

Logic Symbol



# **Truth Table**

Inp	uts	Output
Ā <sub>n</sub>	B <sub>n</sub>	O <sub>n</sub>
L	L	L
L	Н	Н
Н	Х	Z

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = HIGH Impedance

## **Absolute Maximum Ratings**

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only.

Symbol	Parameter	Rating
V <sub>CC</sub>	Supply Voltage	-0.5V to +4.6V
VI	DC Input Voltage	-0.5V to +7.0V
Vo	DC Output Voltage	
	Output in 3-STATE	-0.5V to +7.0V
	Output in HIGH or LOW State <sup>(1)</sup>	-0.5V to +7.0V
I <sub>IK</sub>	DC Input Diode Current, V <sub>I</sub> < GND	–50mA
I <sub>ОК</sub>	DC Output Diode Current, V <sub>O</sub> < GND	–50mA
Ι <sub>Ο</sub>	DC Output Current, $V_O > V_{CC}$	
	Output at HIGH State	64mA
	Output at LOW State	128mA
I <sub>CC</sub>	DC Supply Current per Supply Pin	±64mA
I <sub>GND</sub>	DC Ground Current per Ground Pin	±128mA
T <sub>STG</sub>	Storage Temperature	–65°C to +150°C

Note:

1. I<sub>O</sub> Absolute Maximum Rating must be observed.

## **Recommended Operating Conditions**

The Recommended Operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications. Fairchild does not recommend exceeding them or designing to absolute maximum ratings.

Symbol	Parameter	Min	Max	Units
V <sub>CC</sub>	Supply Voltage	2.7	3.6	V
VI	Input Voltage	0	5.5	V
I <sub>OH</sub>	HIGH-Level Output Current		-32	mA
I <sub>OL</sub>	LOW-Level Output Current		64	mA
T <sub>A</sub>	Free-Air Operating Temperature	-40	85	°C
$\Delta t / \Delta V$	Input Edge Rate, $V_{IN} = 0.8V - 2.0V$ , $V_{CC} = 3.0V$	0	10	ns/V

					$T_A = -4$	0°C to +	85°C	
					Min.	Typ. <sup>(2)</sup>	Max.	1
Symbol	Parameter		V <sub>CC</sub> (V)	Conditions				Units
V <sub>IK</sub>	Input Clamp Diode Volta	ige	2.7	I <sub>I</sub> = -18mA			-1.2	V
VIH	Input HIGH Voltage		2.7–3.6	$V_0 \le 0.1V$ or	2.0			V
VIL	Input LOW Voltage		2.7–3.6	$V_{O} \ge V_{CC} - 0.1V$			0.8	V
V <sub>OH</sub>	Output HIGH Voltage		2.7–3.6	I <sub>OH</sub> = -100μA	V <sub>CC</sub> - 0.2			V
		-	2.7	I <sub>OH</sub> = -8mA	2.4			
		-	3.0	$I_{OH} = -32 \text{mA}$	2.0			1
V <sub>OL</sub>	Output LOW Voltage		2.7	I <sub>OL</sub> = 100μA			0.2	V
				$I_{OL} = 24 \text{mA}$			0.5	
			3.0	$I_{OL} = 16 \text{mA}$			0.4	1
				$I_{OL} = 32 \text{mA}$			0.5	
				$I_{OL} = 64 \text{mA}$			0.55	
I <sub>I(HOLD)</sub>	Bushold Input Minimum	Drive	3.0	$V_{I} = 0.8V$	75			μA
				$V_{I} = 2.0V$	-75			
I <sub>I(OD)</sub>	Bushold Input Over-Drive Current to Change State		3.0	(3)	500			μA
. ,				(4)	-500			
lı	Input Current		3.6	$V_{I} = 5.5V$			10	μA
	Con	trol Pins	3.6	$V_{I} = 0V \text{ or } V_{CC}$			±1	1
	Data	Pins	3.6	$V_I = 0V$			-5	1
				$V_I = V_{CC}$			1	
I <sub>OFF</sub>	Power Off Leakage Cur	rent	0	$0V \le V_I \text{ or } V_O \le 5.5V$			±100	μA
I <sub>PU/PD</sub>	Power up/down 3-STATI Output Current	Ξ	0–1.5	$V_0 = 0.5V$ to 3.0V, $V_1 = GND$ or $V_{CC}$			±100	μA
I <sub>OZL</sub>	3-STATE Output Leakag	e Current	3.6	$V_{O} = 0.5V$			-5	μA
I <sub>OZH</sub>	3-STATE Output Leakag	e Current	3.6	$V_0 = 3.0V$			5	μA
I <sub>OZH</sub> +	3-STATE Output Leakag	e Current	3.6	$V_{CC} < V_O \le 5.5V$			10	μA
I <sub>CCH</sub>	Power Supply Current		3.6	Outputs HIGH			0.19	mA
I <sub>CCL</sub>	Power Supply Current		3.6	Outputs LOW			5	mA
I <sub>CCZ</sub>	Power Supply Current		3.6	Outputs Disabled			0.19	mA
I <sub>CCZ</sub> +	Power Supply Current		3.6	$V_{CC} \le V_O \le 5.5V$ , Outputs Disabled			0.19	mA
$\Delta I_{CC}$	Increase in Power Supp Current <sup>(5)</sup>	ly	3.6	One Input at $V_{CC} - 0.6V$ , Other Inputs at $V_{CC}$ or GND			0.2	mA

# 74LVTH125 — Low Voltage Quad Buffer with 3-STATE Outputs

## Notes:

2. All typical values are at V<sub>CC</sub> = 3.3V,  $T_A = 25^{\circ}C$ .

3. An external driver must source at least the specified current to switch from LOW-to-HIGH.

4. An external driver must sink at least the specified current to switch from HIGH-to-LOW.

5. This is the increase in supply current for each input that is at the specified voltage level rather than  $V_{CC}$  or GND.

# **Dynamic Switching Characteristics(6)**

			Conditions	-	Γ <sub>A</sub> = 25°C	)	
Symbol	Parameter	V <sub>CC</sub> (V)	$C_L = 50 \text{ pF, } R_L = 500\Omega$	Min.	Тур.	Max.	Units
V <sub>OLP</sub>	Quiet Output Maximum Dynamic V <sub>OL</sub>	3.3	(7)		0.8		V
V <sub>OLV</sub>	Quiet Output Minimum Dynamic V <sub>OL</sub>	3.3	(7)		-0.8		V

Notes:

6. Characterized in SOIC package. Guaranteed parameter, but not tested.

7. Max number of outputs defined as (n). n-1 data inputs are driven 0V to 3V. Output under test held LOW.

## **AC Electrical Characteristics**

		$\label{eq:TA} \begin{split} \textbf{T}_{\textbf{A}} = -\textbf{40}^{\circ}\textbf{C} \text{ to } \textbf{+85}^{\circ}\textbf{C},\\ \textbf{C}_{\textbf{L}} = \textbf{50}\textbf{pF}, \ \textbf{R}_{\textbf{L}} = \textbf{500}\Omega \end{split}$					
		Vcc	<sub>2</sub> = 3.3V ± 0	).3V	V <sub>CC</sub> =	= 2.7V	
Symbol	Parameter	Min.	Typ. <sup>(8)</sup>	Max.	Min.	Max.	Units
t <sub>PLH</sub>	Propagation Delay, Data to Output	1.0		3.5	1.0	4.5	ns
t <sub>PHL</sub>	1	1.0		3.9	1.0	4.9	
t <sub>PZH</sub>	Output Enable Time	1.0		4.0	1.0	5.5	ns
t <sub>PZL</sub>	1	1.1		4.0	1.1	5.4	
t <sub>PHZ</sub>	Output Disable Time	1.5		4.5	1.5	5.7	ns
t <sub>PLZ</sub>	1	1.3		4.5	1.3	4.0	
t <sub>OSHL</sub> , t <sub>OSLH</sub>	Output to Output Skew <sup>(9)</sup>			1.0		1.0	ns

Notes:

8. All typical values are at  $V_{CC} = 3.3V$ ,  $T_A = 25^{\circ}C$ .

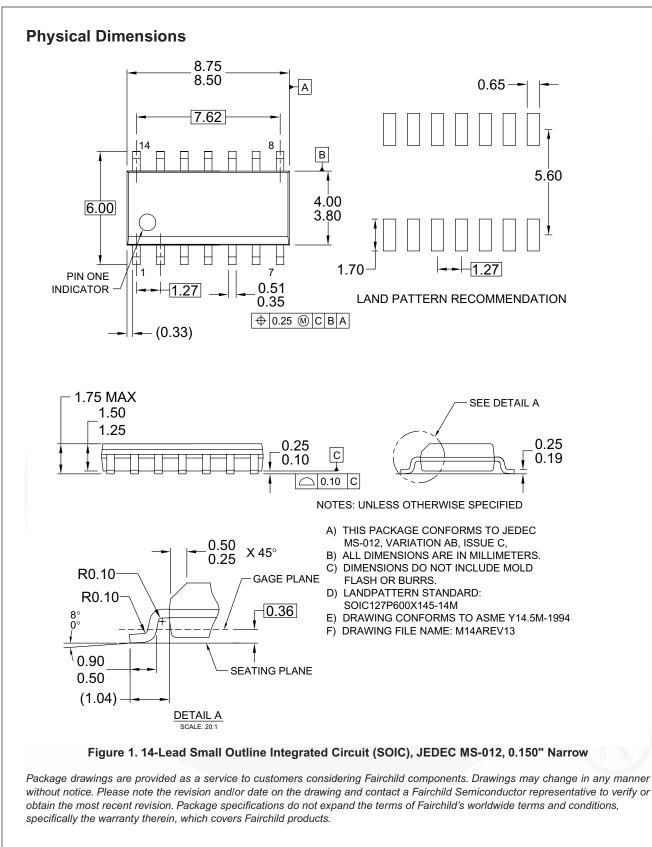
 Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH-to-LOW (t<sub>OSHL</sub>) or LOW-to-HIGH (t<sub>OSLH</sub>).

# Capacitance<sup>(10)</sup>

Symbol	Parameter	Conditions	Typical	Units
C <sub>IN</sub>	Input Capacitance	$V_{CC} = 0V, V_I = 0V \text{ or } V_{CC}$	4	pF
C <sub>OUT</sub>	Output Capacitance	$V_{CC}$ = 3.0V, $V_{O}$ = 0V or $V_{CC}$	8	pF

Note:

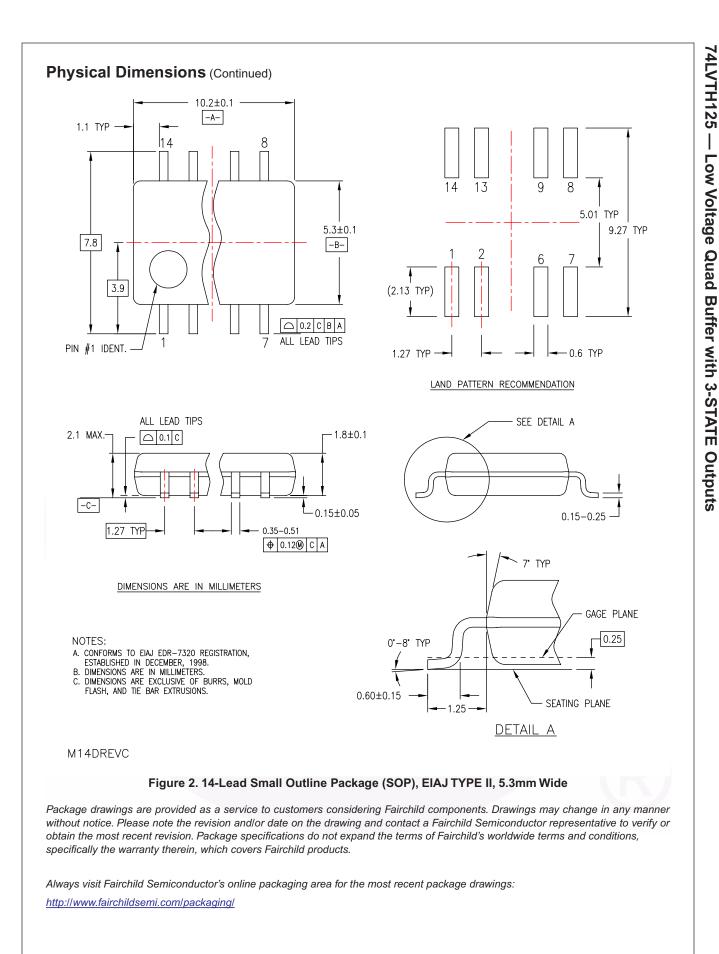
10. Capacitance is measured at frequency f = 1MHz, per MIL-STD-883B, Method 3012.

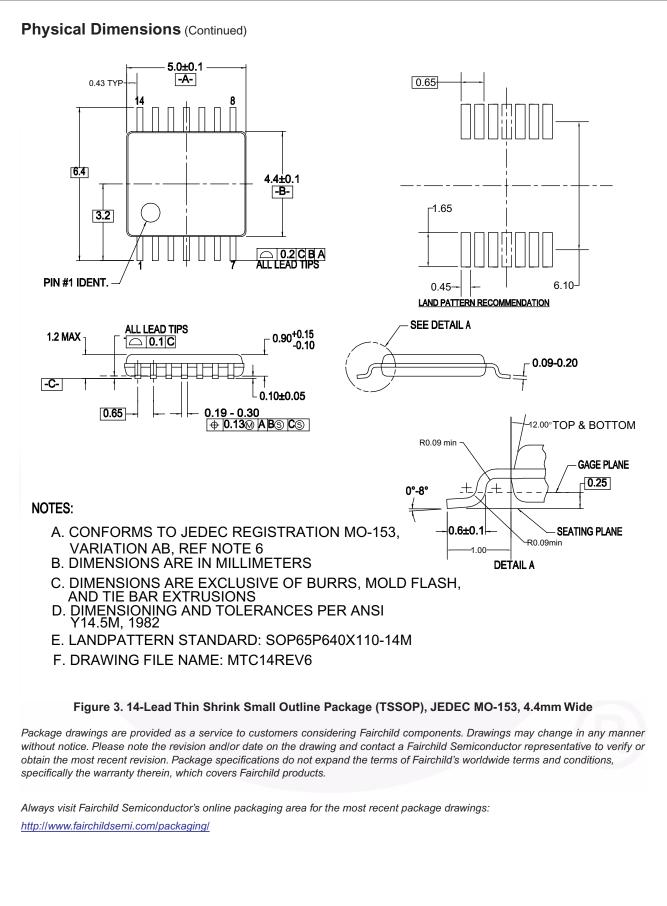


Always visit Fairchild Semiconductor's online packaging area for the most recent package drawings:

http://www.fairchildsemi.com/packaging/

74LVTH125 — Low Voltage Quad Buffer with 3-STATE Outputs





74LVTH125 — Low Voltage Quad Buffer with 3-STATE Outputs



SEMICONDUCTOR

### TRADEMARKS

The following includes registered and unregistered trademarks and service marks, owned by Fairchild Semiconductor and/or its global subsidiaries, and is not intended to be an exhaustive list of all such trademarks.

ACE $x^{@}$ Build it Now <sup>TM</sup> CorePLUS <sup>TM</sup> CROSSVOLT <sup>TM</sup> CTL <sup>TM</sup> Current Transfer Logic <sup>TM</sup> EcoSPARK <sup>®</sup> EZSWITCH <sup>TM</sup> * $\overrightarrow{F}^{@}$ Fairchild <sup>®</sup> Fairchild <sup>®</sup> Fairchild <sup>®</sup> Fairchild Semiconductor <sup>®</sup> FACT Quiet Series <sup>TM</sup> FACT <sup>®</sup> FAST <sup>®</sup> FastvCore <sup>TM</sup>	FPS <sup>™</sup> FRFET <sup>®</sup> Global Power Resource <sup>SM</sup> Green FPS <sup>™</sup> e-Series <sup>™</sup> GTO <sup>™</sup> <i>i-Lo</i> <sup>™</sup> IntelliMAX <sup>™</sup> ISOPLANAR <sup>™</sup> MegaBuck <sup>™</sup> MICROCOUPLER <sup>™</sup> MicroFET <sup>™</sup> MicroPak <sup>™</sup> MillerDrive <sup>™</sup> Motion-SPM <sup>™</sup> OPTOLOGIC <sup>®</sup> OPTOLOGIC <sup>®</sup>	PDP-SPM <sup>™</sup> Power220 <sup>®</sup> POWEREDGE <sup>®</sup> Power-SPM <sup>™</sup> PowerTrench <sup>®</sup> Programmable Active Droop <sup>™</sup> QFET <sup>®</sup> QS <sup>™</sup> QT Optoelectronics <sup>™</sup> Quiet Series <sup>™</sup> RapidConfigure <sup>™</sup> SMART START <sup>™</sup> SPM <sup>®</sup> STEALTH <sup>™</sup> SuperFET <sup>™</sup> SuperSOT <sup>™</sup> 43 SuperSOT <sup>™</sup> 46	SupreMOS <sup>™</sup> SyncFET <sup>™</sup> General The Power Franchise <sup>®</sup> <b>P</b> franchise TinyBoost <sup>™</sup> TinyBuck <sup>™</sup> TinyLogic <sup>®</sup> TINYOPTO <sup>™</sup> TinyPOwer <sup>™</sup> TinyPOwer <sup>™</sup> TinyPWM <sup>™</sup> TinyPWM <sup>™</sup> TinyWire <sup>™</sup> µSerDes <sup>™</sup> UHC <sup>®</sup> Ultra FRFET <sup>™</sup>
FlashWriter <sup>®*</sup>	e control canvar	SuperSOT™-8	VCX™

\* EZSWITCH<sup>TM</sup> and FlashWriter<sup>®</sup> are trademarks of System General Corporation, used under license by Fairchild Semiconductor.

## DISCLAIMER

FAIRCHILD SEMICONDUCTOR RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION, OR DESIGN. FAIRCHILD DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS. THESE SPECIFICATIONS DO NOT EXPAND THE TERMS OF FAIRCHILD'S WORLDWIDE TERMS AND CONDITIONS, SPECIFICALLY THE WARRANTY THEREIN, WHICH COVERS THESE PRODUCTS.

## LIFE SUPPORT POLICY

FAIRCHILD'S PRODUCTS ARE NOT AUTHORIZED FOR USE AS CRITICAL COMPONENTS IN LIFE SUPPORT DEVICES OR SYSTEMS WITHOUT THE EXPRESS WRITTEN APPROVAL OF FAIRCHILD SEMICONDUCTOR CORPORATION.

As used herein:

- which, (a) are intended for surgical implant into the body or (b) support or sustain life, and (c) whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury of the user.
- 1. Life support devices or systems are devices or systems 2. A critical component in any component of a life support, device, or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

Datasheet Identification	Product Status	Definition
Advance Information	Formative or In Design	This datasheet contains the design specifications for product development. Specifications may change in any manner without notice.
Preliminary	First Production	This datasheet contains preliminary data; supplementary data will be published at a later date. Fairchild Semiconductor reserves the right to make changes at any time without notice to improve design.
No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice to improv the design.
Obsolete	Not In Production	This datasheet contains specifications on a product that has been discontinued by Fairchild Semiconductor. The datasheet is printed for reference information only.

## PRODUCT STATUS DEFINITIONS